

# SuperSOT

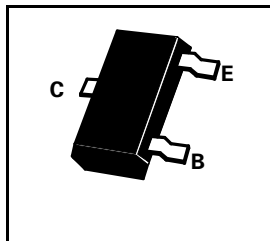
## SOT23 PNP SILICON POWER (SWITCHING) TRANSISTORS

FMMT717 FMMT718  
FMMT720 FMMT722  
FMMT723

ISSUE 3 JUNE 1996

### FEATURES

- \* **625mW POWER DISSIPATION**
- \* **I<sub>C</sub> CONT 2.5A**
- \* I<sub>C</sub> Up To 10A Peak Pulse Current
- \* Excellent h<sub>fe</sub> Characteristics Up To 10A (pulsed)
- \* Extremely Low Saturation Voltage E.g. 10mV Typ.
- \* Exhibits extremely low equivalent on-resistance; R<sub>CE(sat)</sub>



DEVICE TYPE	COMPLEMENT	PARTMARKING	R <sub>CE(sat)</sub>
FMMT717	FMMT617	717	<b>72mΩ at 2.5A</b>
FMMT718	FMMT618	718	<b>97mΩ at 1.5A</b>
FMMT720	FMMT619	720	<b>163mΩ at 1.5A</b>
FMMT722	-	722	-
FMMT723	FMMT624	723	-

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	FMMT 717	FMMT 718	FMMT 720	FMMT 722	FMMT 723	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-12	-20	-40	-70	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-12	-20	-40	-70	-100	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	-5	-5	-5	-5	V
Peak Pulse Current**	I <sub>CM</sub>	-10	-6	-4	-3	-2.5	A
<b>Continuous Collector Current</b>	<b>I<sub>C</sub></b>	<b>-2.5</b>	<b>-1.5</b>	<b>-1.5</b>	<b>-1.5</b>	<b>-1</b>	<b>A</b>
Base Current	I <sub>B</sub>	-500					mA
<b>Power Dissipation at T<sub>amb</sub>=25°C*</b>	<b>P<sub>tot</sub></b>	<b>625</b>					<b>mW</b>
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150					°C

\*Maximum power dissipation is calculated assuming that the device is mounted on a ceramic substrate measuring 15x15x0.6mm

\*\*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%  
Spice parameter data is available upon request for these devices

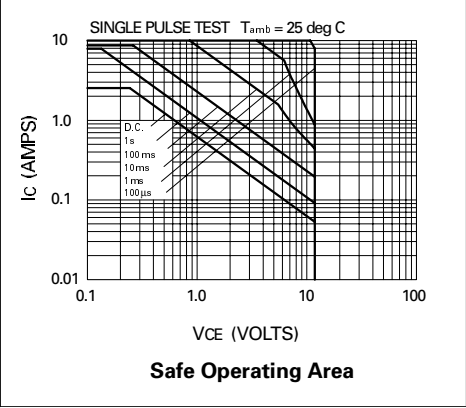
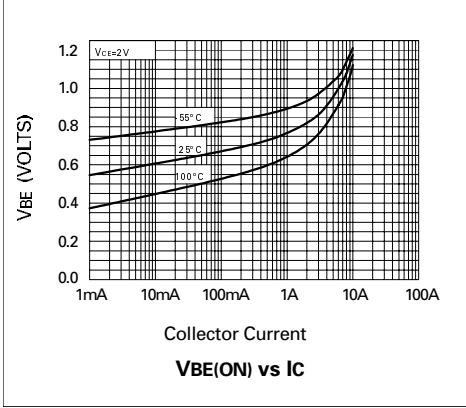
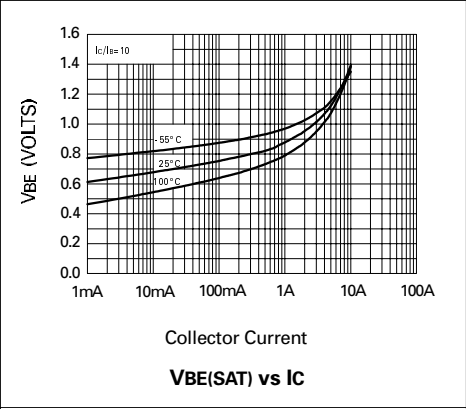
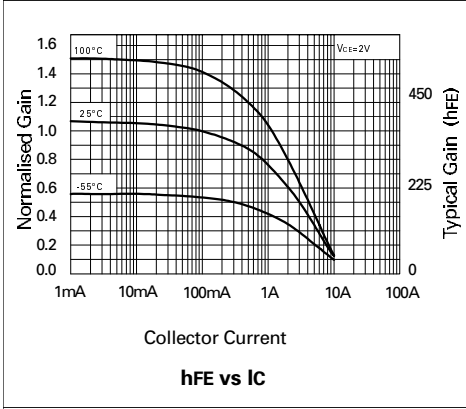
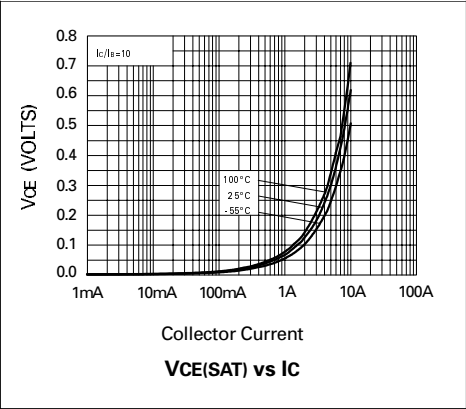
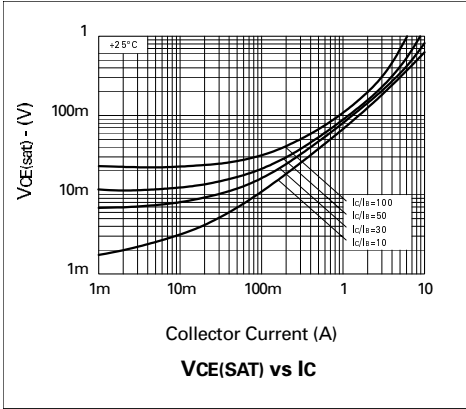
# FMMT717

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-12	-35		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-12	-25		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-8.5		V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			-100	nA	$V_{CB} = -10\text{V}$
Emitter Cut-Off Current	$I_{EBO}$			-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	$I_{CES}$			-100	nA	$V_{CES} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-10 -100 -110 -180	-17 -140 -170 -220	mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -1\text{A}, I_B = -10\text{mA}^*$ $I_C = -1.5\text{A}, I_B = -50\text{mA}^*$ $I_C = -2.5\text{A}, I_B = -50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.0	V	$I_C = -2.5\text{A}, I_B = -50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1.0	V	$I_C = -2.5\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	300 300 180 60 45	475 450 275 100 70			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -100\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -2.5\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -8\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -10\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	$f_T$	80	110		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$		21	30	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		70		ns	$V_{CC} = -6\text{V}, I_C = -2\text{A}$
Turn-Off Time	$t_{(off)}$		130		ns	$I_{B1} = I_{B2} = 50\text{mA}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## TYPICAL CHARACTERISTICS

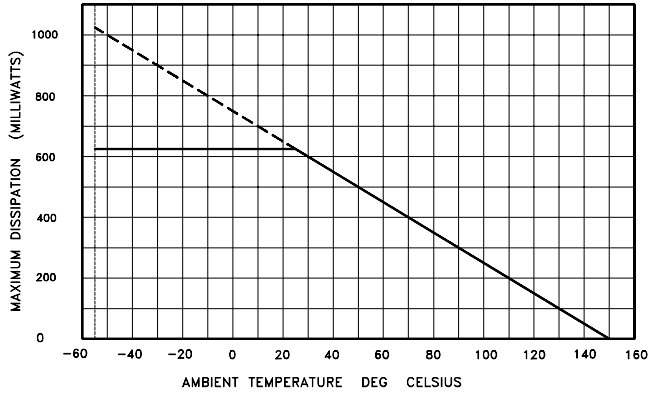


FMMT617 FMMT624  
 FMMT618 FMMT625  
 FMMT619

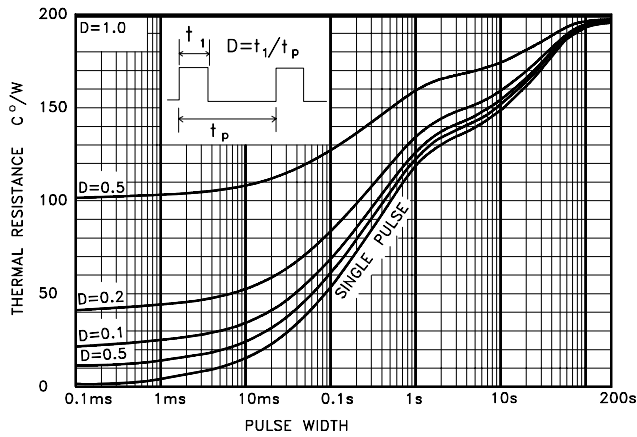
## SuperSOT Series

FMMT717 FMMT722  
 FMMT718 FMMT723  
 FMMT720

### THERMAL CHARACTERISTICS AND DERATING INFORMATION



DERATING CURVE



MAXIMUM TRANSIENT THERMAL RESISTANCE

\* Reference above figures, Devices were mounted on a 15mmx15mm ceramic substrate